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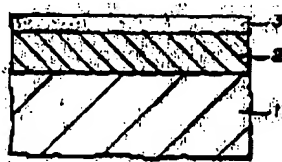
(54) MAGNETO-OPTICAL RECORDING MEDIUM

(57)Abstract:

PURPOSE: To sharpen the shapes of writing pits and to improve C/N at the time of reading out by using a specific artificial lattice film as a recording layer and forming this recording layer on a substrate via a dielectric underlying film.

CONSTITUTION: The artificial lattice film formed by alternately laminating Co layers and Pt layers and/or Pd layers to 50W800 $\text{\AA}$ ; total thickness is used as the recording layer 3. Said recording layer 3 is formed on the substrate 1' via the dielectric underlying film 2. The thickness of the Co layers is preferably 2W8 $\text{\AA}$ ; the thickness of the Pt layers 3W40 $\text{\AA}$ ; and the total thickness 50W400 $\text{\AA}$ ; particularly in case of the artificial lattice film

consisting of a Co-Pt system. The thickness of the Co layers is preferably 1W9 $\text{\AA}$ ; the thickness of the Pd layers 2W40 $\text{\AA}$ ; and the total thickness 50W800 $\text{\AA}$ ; similarly in



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case of the artificial lattice film consisting of a Co-Pd system. While the boundary faces of the respective metallic layers constituting the artificial lattice film are preferably of a superlattice structure, the boundary faces having a modulated structure (compsn. modulated structure) is equally satisfactory. Oxide compds. such as  $Al_2O_3$  or nitride compds. such as ZrN are usable as the material of the dielectric underlying film. The shapes of the writing pits are thereby sharpened and the C/N at the time of reading out is improved.

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